

Abstract

Method for producing a vertically emitting laser

The invention is based on the object of specifying a method which makes it possible to produce VCSEL lasers with even better optical properties than heretofore.

This object is achieved by means of a method for producing a vertically emitting laser, in which a current aperture and a semiconductor relief are produced, the area size of the semiconductor relief and the area size of the current aperture being defined in the same production step.

Figure 8